

Appl. No. 10/650,505  
Amdt. Dated December 19, 2005  
Reply to Office Action of September 19, 2005

Attorney Docket No. 81872.0051  
Customer No.: 26021

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-12. (Canceled)

13. (Currently amended) A dry etching method for forming fine textures on a surface of a substrate to be etched, said dry etching method comprising:

placing a substrate to be etched ~~on an RF electrode provided inside a chamber, directly or through a tray;~~ and

covering said substrate to be etched with a plate,

wherein said plate ~~is provided~~ comprises an obstacle with a planar or nearly planar plurality of obstacle forming members that inhibit, inhibit a part of gas and plasma from passing through said plate.

14. (Previously presented) The dry etching method according to Claim 13, wherein said substrate to be etched is made of silicon.

15. (Original) The dry etching method according to Claim 13, wherein said plate covers said substrate to be etched while securing a distance of 5 mm to 30 mm.

16-17. (Canceled)

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18. (Currently amended) A dry etching method, comprising:  
placing a substrate to be etched on an RF electrode provided inside a  
~~chamber, directly or through a tray;~~ and  
covering said substrate to be etched with a plate provided with a number of  
opening portions,  
wherein fine textures are formed on a surface of said substrate to be etched  
and said plate is cleaned on a surface side concurrently.

19. (Original) The dry etching method according to Claim 18, wherein said  
dry etching method is a reactive ion etching method.

20. (Currently amended) The dry etching method according to Claim 18,  
wherein a substrate to be etched next is placed inside a chamber, with said plate  
positioned such that with a surface and a back surface of said plate being are  
reversed after said plate is cleaned on the surface side, and fine textures are formed  
on a surface of said substrate to be etched next.

21-22. (Cancelled)

23. (New) The dry etching method according to Claim 13, wherein an  
opening portion is provided between neighboring obstacle forming members.

24. (New) The dry etching method according to Claim 23, wherein an open  
area ratio of said obstacle is 5 to 40%.

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25. (New) The dry etching method according to Claim 13, wherein said obstacle forming members are a plurality of long members aligned with a clearance in between.

26. (New) The dry etching method according to Claim 25, wherein said long member is a bar-shaped or sheet member.

27. (New) The dry etching method according to Claim 13, wherein said obstacle forming member comprises a mesh woven by crossing said plurality of long members over and under with each other.

28. (New) The dry etching method according to Claim 13, wherein said obstacle comprises a plurality of obstacles of a laminated structure.

29. (New) The dry etching method according to Claim 28, wherein said obstacle comprises a member formed by laminating a plurality of long members aligned with a clearance in between, in different directions.

30. (New) The dry etching method according to Claim 13, wherein said obstacle forming member is made of one kind or a combination of two or more kinds selected from a group consisting of materials (a), (b), and (c) as follows:

- (a) a glass-based material;
- (b) a metal material; and
- (c) a resin material.

31. (New) The dry etching method according to Claim 30, wherein said metal material is an aluminum-based material.

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32. (New) The dry etching method according to Claim 18, wherein said plate is structured in such a manner that a surface and a back surface can be reversed.

33. (New) The dry etching method according to Claim 32, wherein the surface and the back surface of said plate are of substantially a same shape.

34. (New) A dry etching method for forming fine textures on a surface of a substrate to be etched, said dry etching method comprising:

placing a substrate to be etched inside a chamber, and  
covering said substrate to be etched with a plate comprising an obstacle that inhibits a part of a gas and plasma from passing through said plate,  
wherein a member forming said obstacle is provided with a number of opening portions.

35. (New) The dry etching method according to Claim 34, wherein an open area ratio of said obstacle is 5 to 40%.

36. (New) The dry etching method according to Claim 34, wherein said substrate to be etched is made of silicon.

37. (New) The dry etching method according to Claim 34, wherein said plate covers said substrate to be etched while securing a distance of 5 mm to 30 mm.

38. (New) The dry etching method according to Claim 34, wherein said dry etching method is a reactive ion etching method.

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39. (New) The dry etching method according to Claim 34, wherein said obstacle is made of one kind or a combination of two or more kinds selected from a group consisting of materials (a), (b), and (c) as follows:

- (a) a glass-based material;
- (b) a metal material; and
- (c) a resin material.

40. (New) The dry etching method according to Claim 39, wherein said metal material is an aluminum-based material.